

| VRRM | IF (TC≤135℃) | QC |
|------|---------------|------|
| 650V | 11A | 23nC |

Applications:

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Features:

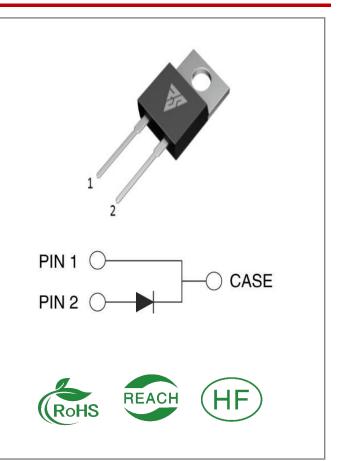
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Ordering Information

| Part Number | Package | Marking Packing | | Qty. |
|-------------|----------|-----------------|------|--------|
| RSS08065A | TO-220-2 | RSS08065A | Tube | 50 PCS |





Maximum Ratings (TJ= 25° C unless otherwise specified)

| Symbol | Parameter | Value | Unit | Test Conditions | Note |
|-------------|---|---------------|------|---|-------|
| VRRM | Repetitive Peak Reverse Voltage | 650 | V | TC = 25℃ | |
| VRSM | Surge Peak Reverse Voltage | 650 | V | TC = 25℃ | |
| VR | DC Blocking Voltage | 650 | V | TC = 25℃ | |
| IF | Forward Current | 25 11 8 | А | TC ≤ 25℃ TC ≤ 135℃ TC ≤ 154℃ | Fig.3 |
| IFSM | Non-Repetitive Forward Surge Current | 76 68 | A | TC = 25℃, tp = 10ms, Half Sine Wave TC = 110℃, tp = 10ms, Half Sine Wave | |
| IFRM | Repetitive Peak Forward Surge Current | 67 | А | TC = 25° C, tp = 10ms, Half Sine Wave | |
| Ptot | Power Dissipation | 100 | W | TC = 25 ℃ | Fig.4 |
| ТС | Maximum Case Temperature | 154 | °C | | |
| TJ,TST G | Operating Junction and Storage Temperature | -55 to175 | °C | | |

Electrical Characteristics (TJ= 25°C unless otherwise specified)

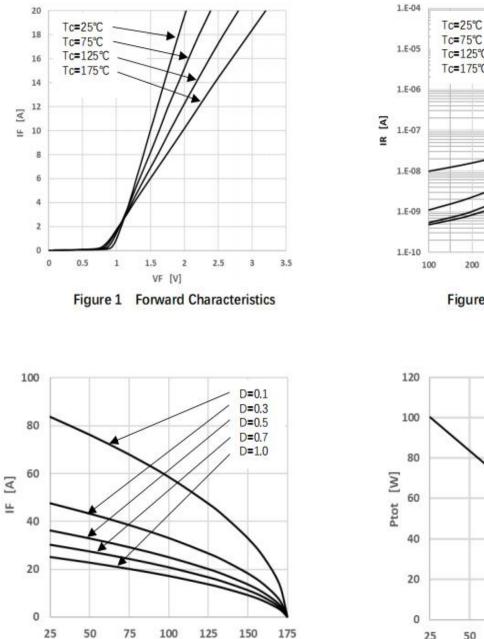
| Symbol | Parameter | Тур. | Max. | Unit | Test Conditions | Note |
|--------|------------------------------|-----------------|----------|------|---|-------|
| VF | Forward Voltage | 1.39 1.74 | 1.6 - | V | IF = 8A, TJ = 25℃ IF = 8A, TJ = 175℃ | Fig.1 |
| IR | Reverse Current | 6 12 | 60 - | μΑ | VR = 650V, TJ = 25℃ VR = 650V, TJ = 175℃ | Fig.2 |
| с | Total Capacitance | 338 44 43 | / | pF | VR = 1V, TJ = 25℃, f = 1MHz VR = 200V, TJ = 25℃, f = 1MHz VR = 400V, TJ = 25℃, f = 1MHz | Fig.5 |
| QC | Total Capacitive Charge | 23 | / | nC | VR =400V, | Fig.6 |
| Ec | Capacitance Stored Energy | 3.7 | | uJ | VR =400V, | Fig.7 |

Thermal Characteristics (TJ= 25° C unless otherwise specified)

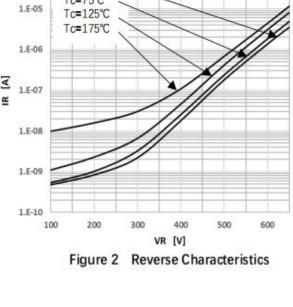
| Symbol | Parameter | Тур. | Unit | Note |
|--------|--|-------|------|-------|
| RθJC | Thermal Resistance from Junction to Case | 1.495 | °C/W | Fig.8 |

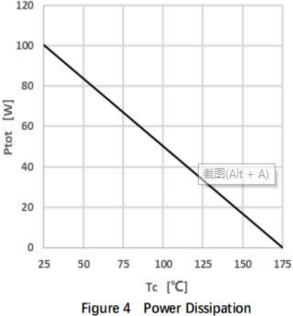


Typical Feature Curve



Tc [℃] Figure 3 Peak Forward Current Derating







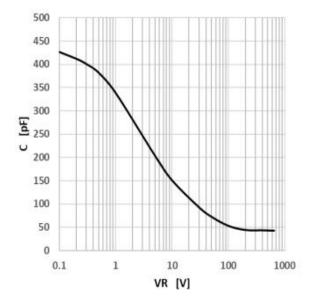


Figure 5 Capacitance vs. Reverse Voltage

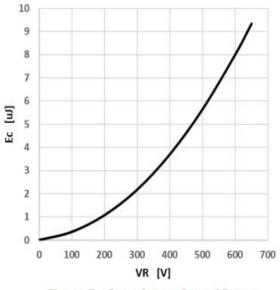


Figure 7 Capacitance Stored Energy

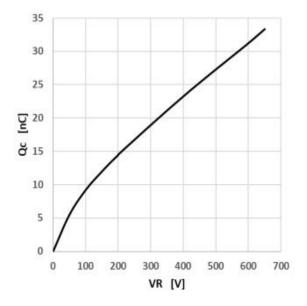
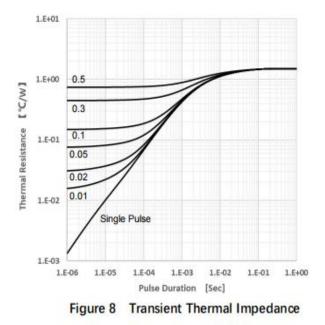
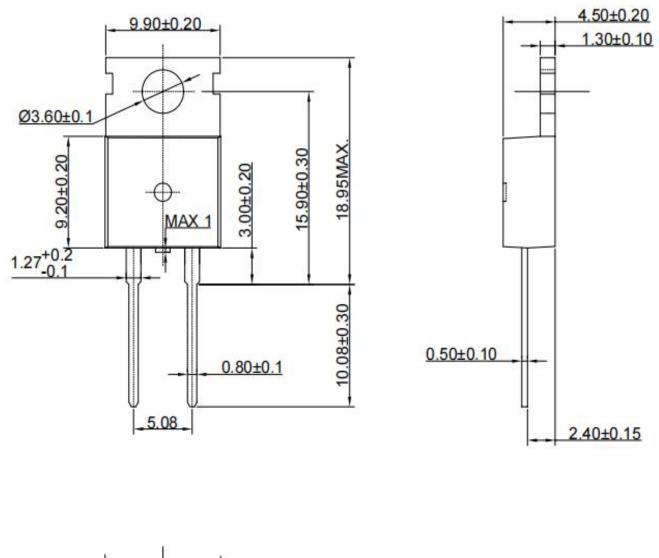


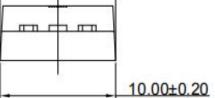
Figure 6 Capacitance Charge vs. Reverse Voltage





Package outline drawing(TO-220 Unit: mm)







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